EAST - [10718310 deep trench DRAM with peripheral circuit.wsp:1]

File View Edit Tools Window Help

- BRS: 32with 33
- Pending
- Active
  - L1: (1) 10/718310
  - L2: (6) 5519236.pn. "20020127803" "20020127786"
  - L3: (1342) (semiconductor active) adj (strip$4 web)
  - L4: (17333) second adj2 well
  - L5: (554) (257/302).CCLS.
  - L6: (10) 4 and 5
  - L7: (17854) first adj2 well
  - L8: (73343) "same" near2 (conduct$4 impurity dop$4)
  - L9: (4658) 4 with 7
  - L10: (48) 9 with 8
  - L11: (45548) (wordline "WL" (word near (read$3 writ$3)))
  - L12: (3216814) contact
  - L13: (0) 10 with 11
  - L14: (5090) deep adj trench
  - L15: (715) buried adj strap
  - L16: (180) 14 near9 15
  - L17: (3149775) identical similar $2
  - L18: (5) (17 "same") with 16
  - L19: (1) 09/607217
  - L20: (20) 2 6 18
- Failed
- Saved
  - (1) 09/948877
  - (1738) "KONINKLIJKE PHILIPS ..."

Search Clear Browse Queue Clear

DBs USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

Default operator: OR

Plurals

Highlight all hit terms initially

2 6 18

Aug 2004

	U	T	Inventor	Document I	Issue	P	Title	Current	Current XR	Retrieval	S	C	P	2	3	4	5	Image Doc.	P
1			Bostelmann,	US 6344390	20020	2	Methods of forming the buried strap and its q	438/249	257/E21.65									US 634439	
2			Kowalski, Be	US 2004010	20040	9	Transistor array and semiconductor memory	257/302										US 200401	
3			Losee, Becky	US 2002019	20021	1	Method for etching silicon trenches	438/709	257/302;									US 200201	
4			Schlosser, Til	US 2002012	20020	1	Method for producing a memory cell for a se	438/258	257/E21.65									US 200201	
5			Hofmann, Fra	US 2002012	20020	1	Method for producing a cell of a semiconduct	438/243	257/E21.65									US 200201	
6			Kim, Ho-Hyun	US 2002008	20020	1	MOS control diode and method for manufact	257/135	257/242;									US 200200	
7			Wu, Xiaoju et	US 2002007	20020	1	Electronic circuit with electrical hole isolato	257/302	257/E21.37									US 200200	
8			Hsu, Louis L.	US 2002007	20020	1	Structure and method for creating vertical c	257/302	257/E23.14									US 200200	
9			Schroeder, H	US 6747303	20040	1	CHARGE DETECTOR SEMICONDUCTOR CO	257/296	257/297;									US 674730	
10			Seitz, Mihel	US 6706634	20040	7	Control of separation between transfer gate	438/692	257/E21.65									US 670663	

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